

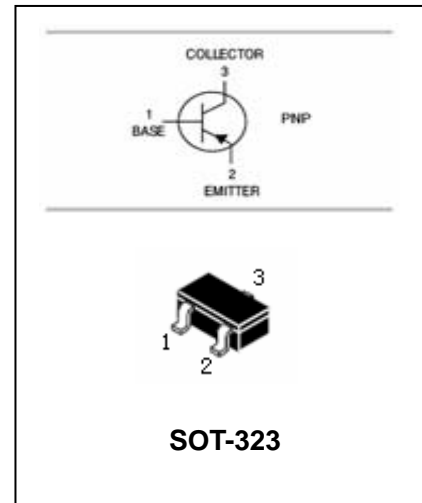


PNP Silicon Epitaxial Planar Transistor

2SA1576A

FEATURES

- Power dissipation.($P_C=200\text{mW}$)
- Excellent H_{FE} Linearity.
- Complements the 2SC4081.



APPLICATIONS

- General purpose application.
- Switching and amplification.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1576A	FQ/FR/FS	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Dissipation	200	mW
T_{stg}	Storage Temperature	-55 to +150	$^\circ\text{C}$
T_j	Junction Temperature	150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.5	V
Transition frequency	f_T	$V_{CE} = -12V, I_C = -2mA$ $f = 30MHz$	140			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -12V, I_E = 0, f = 1MHz$		4	5	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560
marking	FQ	FR	FS

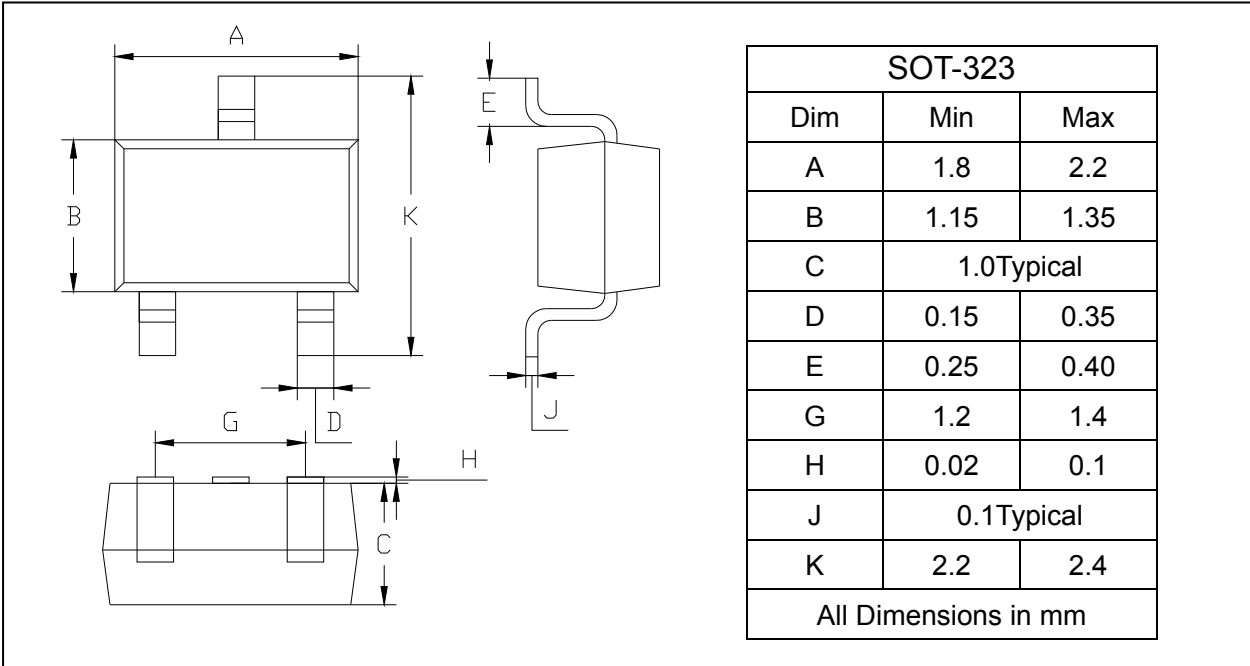
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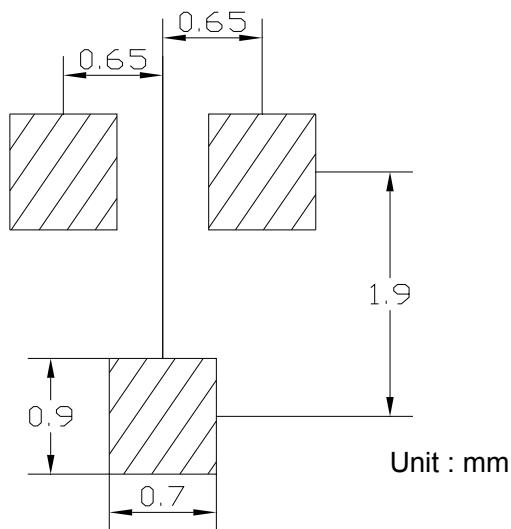
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SA1576A	SOT-323	3000/Tape&Reel